IC Failure Analysis Lab

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Failure Analysis Report

ICFA Lab Reference Number:	ICFA-0003 - Final		
Customer:			
Customer Reference Number:	N/A		
Requester:	Paul G.		
Device Number:	MC68194FJ		
Quantity:	3 + 2 Ref		
Report Date:	September 19, 2010		
Analyst:	Fenimore C.		
Report By:	Fenimore C.		

Description

Three (3) Motorola / On Semi Carrier Band Modem (MC68194FJ and two (2) reference samples were submitted to the IC Failure Analysis Lab for failure analysis. The customer reported failure is listed below. Samples were serialized by ICFA Lab.

Device Information

Serial Number	Top Marking	Customer Reported Failure Description		
F1	ON MC68194FJ ZRED0240 PHILIPPINES	"Does not work – Replaced the chip and Module worked"		
F2	ON MC68194FJ ZRED0240 PHILIPPINES	"Does not work – Replaced the chip and Module worked"		
F3	M MC68194FJ ZRAY0512 PHILIPPINES	"Does not work – Replaced the chip and Module worked"		
G4 ~ G5 (Reference)	ON MC68194FJ ZRAY0512 PHILIPPINES	Good		

Summary

External visual inspection and real time 2D X-Ray of the failing samples revealed no anomaly. No wire bonds are visible on the X-Ray images because they are Aluminum. T-SAM (Through- Scanning Acoustic Microscopy) revealed anomaly on F3 sample.

I-V curve trace of samples revealed opens/shorts and anomaly to GND pins. All four 4 GND pins (Pins 1, 39, 43 and 48) were tied together and used as a single GND for our I-V curve testing. *This was done to minimize curve tracing costs and identify the suspected pins.*

The suspected pins identified from the above method were individually curve traced to each GND pin. The results of this analysis revealed shorts and leakage on suspected pins.

All 3 failing samples were decapsulated and no anomaly was observed on die surfaces. The samples were inspected under OBRICH microscope and emission sites were observed on all 3 failing samples.

F1 & F2 samples were randomly selected and mechanically delayered down to the Contact layer. An anomaly sites were observed in the Contact layers near pins 34 ~ 38 of F1 and pins 37 & 38 of F2 samples. The most likely cause of anomalies in the Contact planes is ESD (Electrostatic Discharge) in both samples.

F3 sample was also mechanically delayered down to substrate layer. An anomaly was observed in the substrate layer. The most likely cause of anomaly in the substrate layer is ESD (Electrostatic Discharge).

ICFA-0003 - (MC68194FJ) - Final

Analyses

External Visual Examination:

External visual inspections of the failing samples revealed no anomaly. (Figure 1 ~ 2)

2D X-ray inspection:

Real time 2D X-Ray of samples revealed no anomaly. No wire bonds are visible because wire bonds are Aluminum. (Figures $3 \sim 4$)

Scanning Acoustic Microscopy (SAM):

T-SAM inspection revealed anomaly on F3 Sample. (Figure 5)

Electrical I-V Testing:

The electrical characteristics of failing samples were compared to the reference sample with a curve tracer.

The results are as below: (Figures 6 ~ 24)

		2012	Results		
Pin#	Pin # Pin name	GND	F1	F2	F3
Pin4	RXCLK				
Pin5	SMIND				
Pin6	RXSYMO				
Pin7	RXSYMI				
Pin8	RXSYM2				
Pin10	VCC-TTL				
Pin11	GND-TTL				
Pin12	RESET				
Pin13	TXSYMO				
Pin14	TXSYM1				
Pin15	TXSYM2	To Pins (1+39+43+48)			
Pin16	SMREQ				
Pin17	TXCLK				High Resistance Open
Pin18	JAB				
Pin19	EOTDIS				
Pin20	VCC-OSC				
Pin21	XTAL2				
Pin22	XTAL1				
Pin23	GND-OSC				
Pin24	TXDIS		Leakage (curve unstable)	Leakage (curve unstable)	
Pin25	GND- LOGIC				
Pin26	TXOUT				

F1, F2 and F3 => I-V Curve Trace Results. Pins 1, 39, 43 and 48 were Table 1: tied together and used as single GND point for the I-V test.

Electrical I-V Testing Results (Continued)

		Results			
Pin#	Pin name	GND	F1	F2	F3
Pin27	VCC-TXOUT		Leakage (curve unstable)		
Pin28	TXOUT		,		
Pin29	JAB-RC				
Pin30	GAIN		Leakage		
Pin31	CARDET		Leakage		
Pin32	VCC-RCV		Short		
Pin33	GND-RCV				
Pin34	THRESHOLD				
Pin35	FDBK		Short	Leakage	Leakage
Pin36	FDBK		Short	Leakage	Leakage
Pin37	RXIN		Short	Leakage	Leakage
Pin38	RXIN	To Pins (1+39+43+48)	Short	Leakage	Leakage
Pin40	SET-PW	(1133143140)			
Pin41	RPW				
Pin42	CPW				
Pin44	VCX				Leakage
Pin45	VCM-C1				
Pin46	VCM-C2				
Pin47	VCC-VCM				
Pin50	DOWN				
Pin51	UP				
Pin52	VCC-LOGIC				

F1, F2 and F3 => I-V Curve Trace Results. Pins 1, 39, 43 and 48 were Table 2: tied together and used as single GND point for the I-V test.

Pin #	Din nama	CND	Results of Suspected Pins to Individual GNDs			
Pin # Pin name	Pin name	GND	F1	F2	F3	
Pin24	TXDIS		Leakage (curve unstable)	Leakage (curve unstable)	No analysis	
Pin27	VCC-TXOUT		Leakage (curve unstable)	No analysis	No analysis	
Pin30	GAIN		Slight Leakage	No analysis	No analysis	
Pin31	CARDET	to Pin1	Leakage	No analysis	No analysis	
Pin32	VCC-RCV	lo Fiiii	Short	No analysis	No analysis	
Pin35	FDBK		Short	Leakage	Leakage	
Pin36	FDBK		Short	Leakage	Leakage	
Pin37	RXIN		Short	Leakage	Leakage	
Pin38	RXIN		Short	Leakage	Leakage	
Pin44	VCX		No analysis	No analysis	Leakage	
Pin24	TXDIS				No analysis	
Pin27	VCC-TXOUT			No analysis	No analysis	
Pin30	GAIN			No analysis	No analysis	
Pin31	CARDET	to Dingo		No analysis	No analysis	
Pin32	VCC-RCV	to Pin39		No analysis	No analysis	
Pin35	FDBK]			-	
Pin36	FDBK]				
Pin37	RXIN]				
Pin38	RXIN					
Pin44	VCX		No analysis	No analysis		

Table 3: F1, F2 and F3 => Re-do of I-V Curve Trace Results. Suspected pins are curve traced to individual GNDs (Pin 1 and Pin 39).

Din #	Pin name	GND	Results of Suspected Pins to Individual GNDs			
Pin #			F1	F2	F3	
Pin24	TXDIS				No analysis	
Pin27	VCC-TXOUT			No analysis	No analysis	
Pin30	GAIN			No analysis	No analysis	
Pin31	CARDET	to Pin43		No analysis	No analysis	
Pin32	VCC-RCV	10 F11143		No analysis	No analysis	
Pin35	FDBK					
Pin36	FDBK					
Pin37	RXIN					
Pin38	RXIN					
Pin44	VCX		No analysis	No analysis		
Pin24	TXDIS		Leakage (curve unstable)	Leakage (curve unstable)	No analysis	
Pin27	VCC-TXOUT		Leakage (curve unstable)	No analysis	No analysis	
Pin30	GAIN		Slight leak	No analysis	No analysis	
Pin31	CARDET	to Pin48	Leakage	No analysis	No analysis	
Pin32	VCC-RCV	10 F11146	Leakage	No analysis	No analysis	
Pin35	FDBK		Leakage	Leakage	Leakage	
Pin36	FDBK		Leakage	Leakage	Leakage	
Pin37	RXIN		Leakage	Leakage	Leakage	
Pin38	RXIN		Leakage	Leakage	Leakage	
Pin44	VCX		No analysis	No analysis	Leakage	

Table 4: F1, F2 and F3 => Re-do of I-V Curve Trace Results. Suspected pins are curve traced to individual GNDs (Pin 43 and Pin 48).

Decapsulation and Die Optical Inspection:

All 3 failing samples were mechanically decapped and no anomaly was observed on die surfaces. (Figure 25)

OBRICH and Photo Emission Inspection:

All decapped failing samples and a reference sample were powered under an OBRICH scope to look for photo emission (hot spots) sites. Hot spots were observed on all 3 failing samples. (Figures 26 ~ 28)

Mechanical Delayering and SEM Inspection:

F1 & F2 samples were randomly selected and mechanically delayered down to the Contact layer. An anomaly sites were observed in the Contact layers near pins 34 ~ 38 of F1 and pins 37 & 38 of F2 samples. The most likely cause of anomalies in the Contact planes is ESD (Electrostatic Discharge) in both samples. (Figures 29 ~ 38)

F3 sample was also mechanically delayered down to substrate layer. An anomaly was observed in the substrate layer. The most likely cause of anomaly in the substrate layer is ESD (Electrostatic Discharge). (Figures 39 ~ 44)

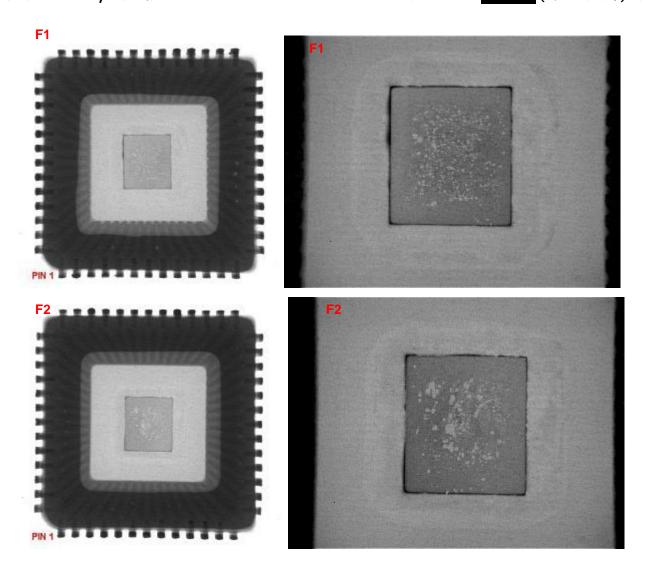
Photographs:



Figure 1: Photographs of Failing samples as received



Figure 2: Photographs of Reference samples as received



F1 and F2 => 2D X-Ray of sample exhibit no anomaly. Close up image is on the right Figure 3:

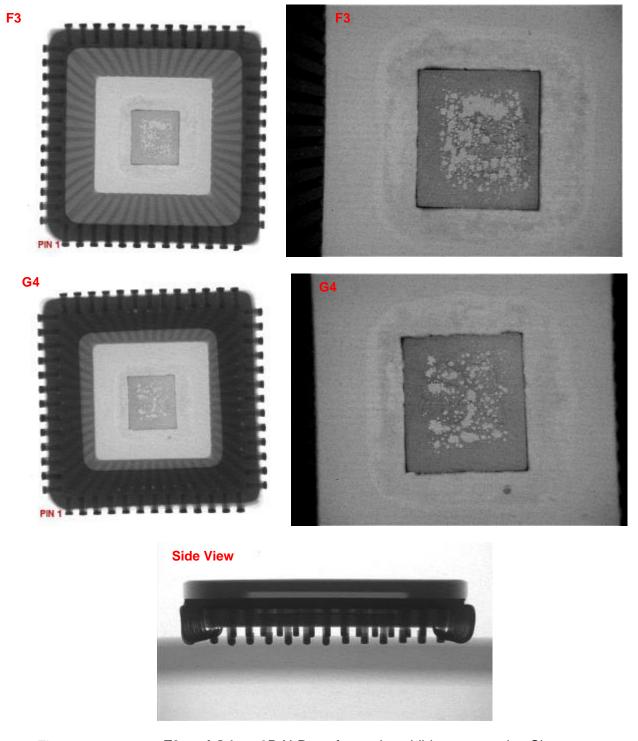


Figure 4: **F3 and G4** => 2D X-Ray of sample exhibit no anomaly. Close images are on the right.

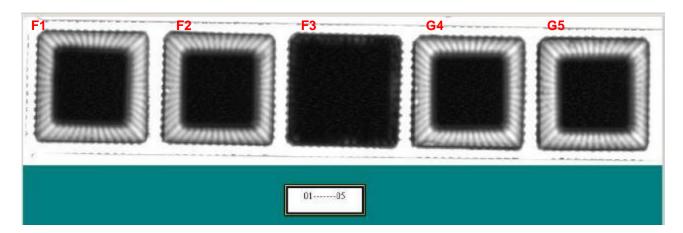


Figure 5: T-SAM results revealed anomaly on F3 sample. Anomaly is represented in dark color.

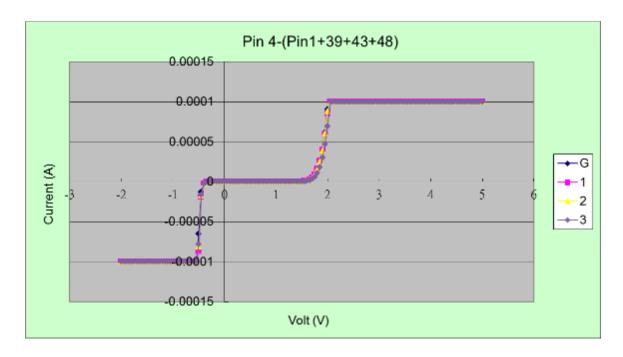


Figure 6: Typical I-V Curve of a good pin (Pin4) to GND (Pins 1+39+43+48). No anomaly was observed.

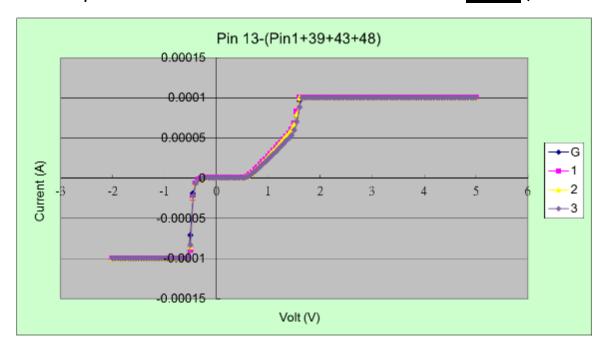
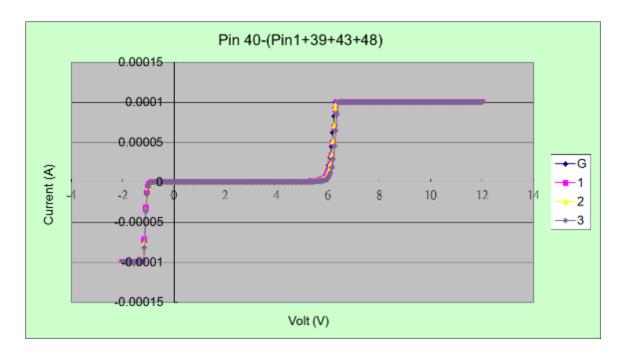


Figure 7: Typical I-V Curve of a good pin (Pin13) to GND (Pins 1+39+43+48). No anomaly was observed.



Typical I-V Curve of a good pin (Pin40) to GND (Pins 1+39+43+48). Figure 8: No anomaly was observed.

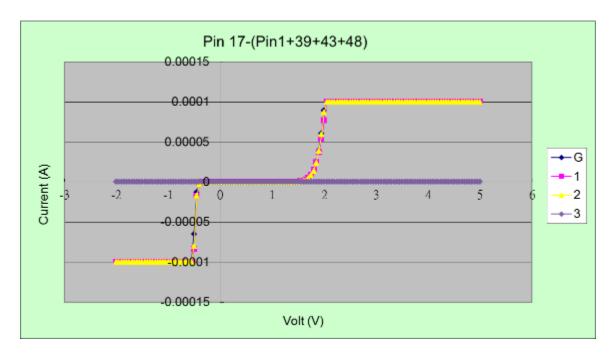


Figure 9: Typical I-V Curve of an abnormal pin (Pin 17) to GND (Pins 1+39+43+48). Open was observed on **F3** sample.

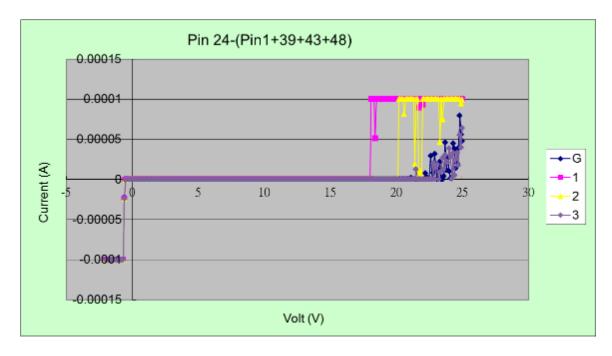
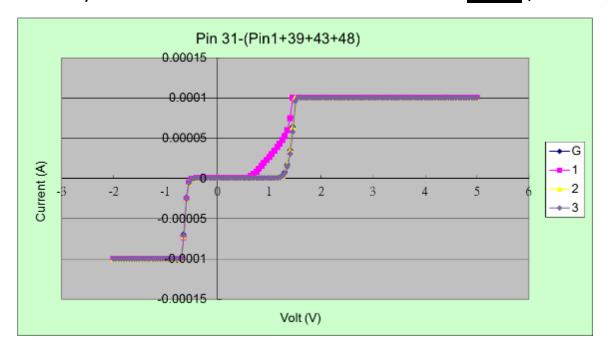
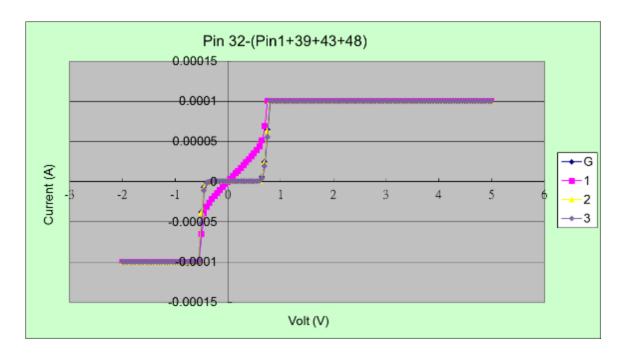


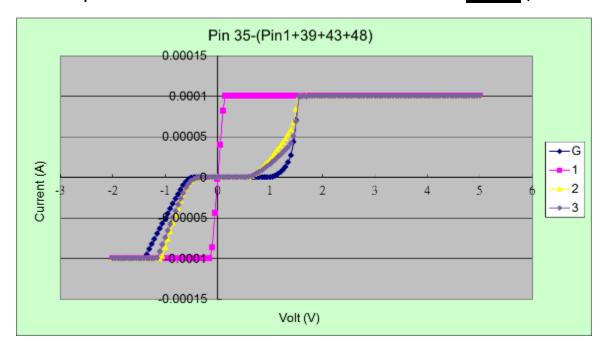
Figure 10: Typical I-V Curve of an unstable pin (Pin 24) to GND (Pins 1+39+43+48). Unstable condition was observed on **F1 & F2** samples.



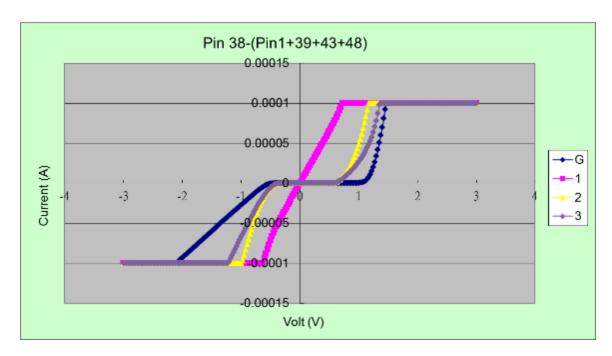
Typical I-V Curve of a leaking pin (Pin 31) to GND (Pins Figure 11: 1+39+43+48). Leakage was observed on **F1** sample.



Typical I-V Curve of a shorted pin (Pin 32) to GND (Pins Figure 12: 1+39+43+48). Short was observed on **F1** sample.



Typical I-V Curve of a shorted pin (Pin 35) to GND (Pins Figure 13: 1+39+43+48). Short was observed on **F1** sample.



Typical I-V Curve of a shorted and leaking pin (Pin 38) to GND (Pins Figure 14: 1+39+43+48). Short and leakage were observed on **F1 and F2 & F3**, respectively.

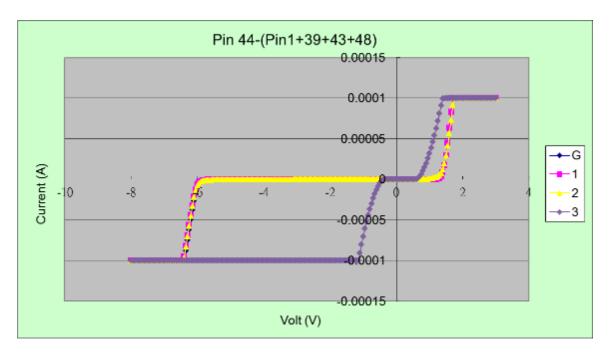


Figure 15: Typical I-V Curve of a leaking pin (Pin 44) to GND (Pins 1+39+43+48). Leakage was observed on **F3** sample.

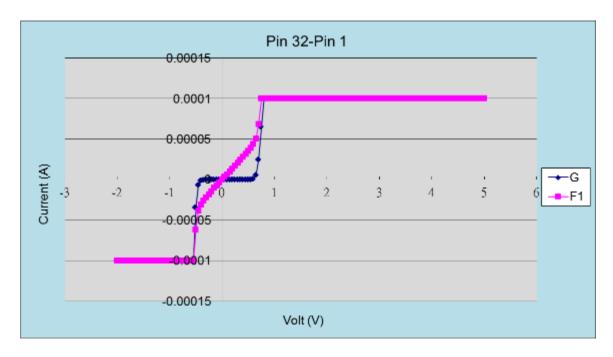


Figure 16: F1 => Typical I-V Curve of a shorted pin (Pin 32) to GND (Pin1).

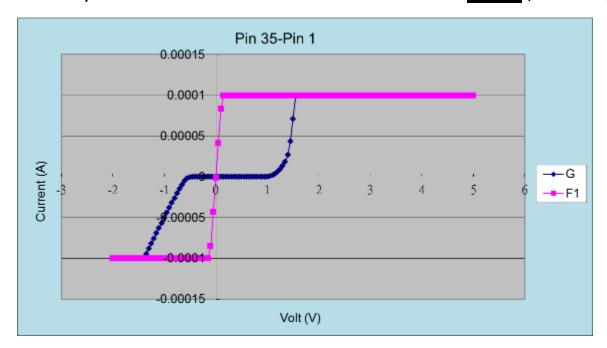


Figure 17: F1 => Typical I-V Curve of a shorted pin (Pin 35) to GND (Pin1).

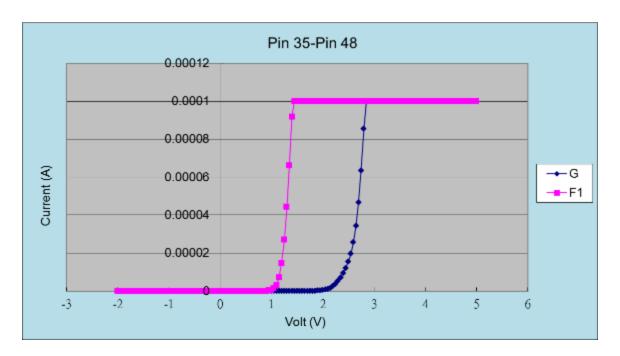


Figure 18: F1 => Typical I-V Curve of a leaking pin (Pin 35) to GND (Pin 48).

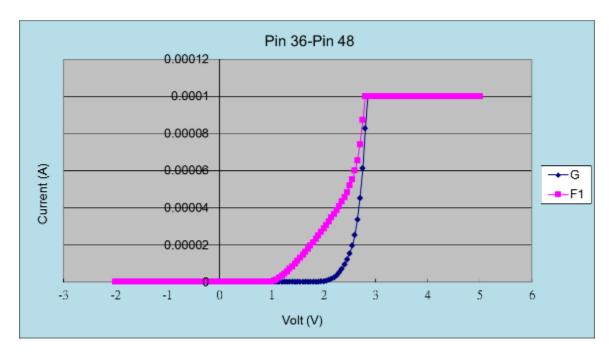


Figure 19: **F1** => Typical I-V Curve of a leaking pin (Pin 36) to GND (Pin 48).

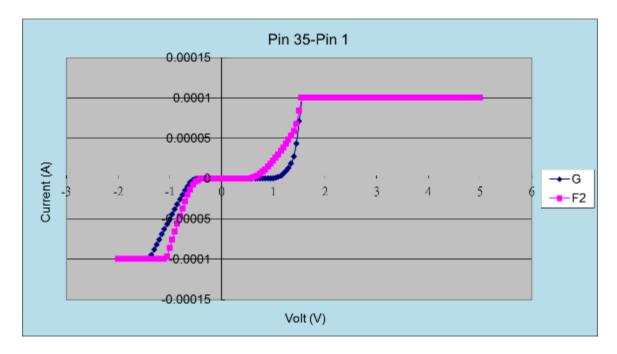


Figure 20: F2 => Typical I-V Curve of a leaking pin (Pin 35) to GND (Pin 1).

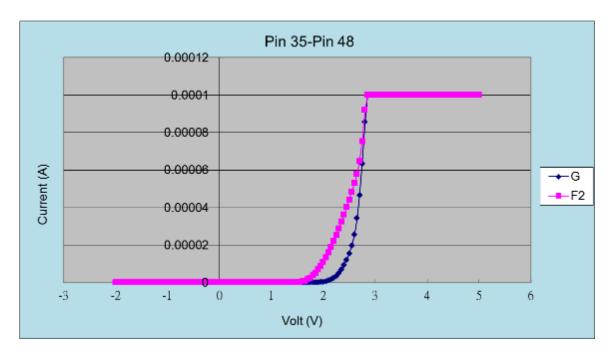


Figure 21: F2 => Typical I-V Curve of a leaking pin (Pin 35) to GND (Pin 48).

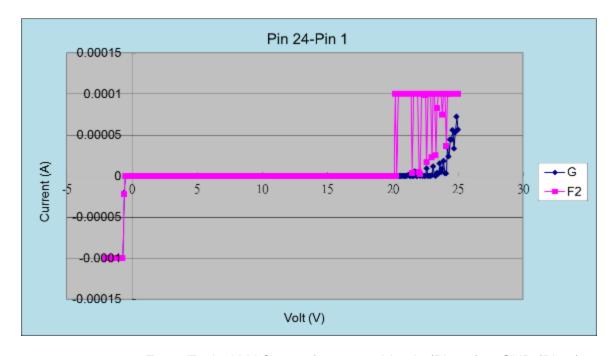


Figure 22: F2 => Typical I-V Curve of an un-stable pin (Pin 24) to GND (Pin 1).

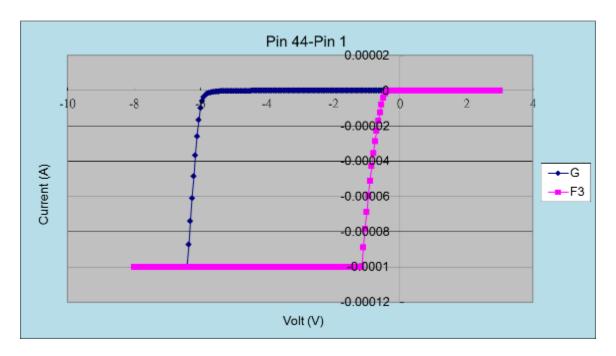


Figure 23: F3 => Typical I-V Curve of a leaking pin (Pin 44) to GND (Pin 1).

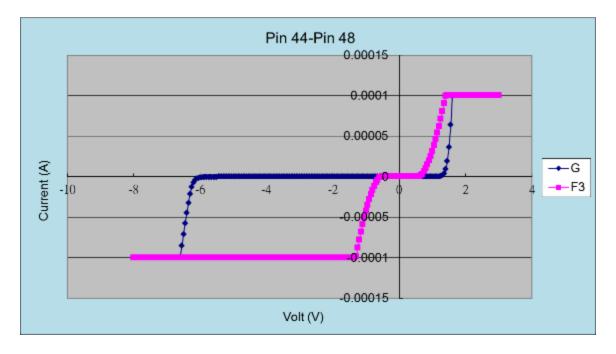
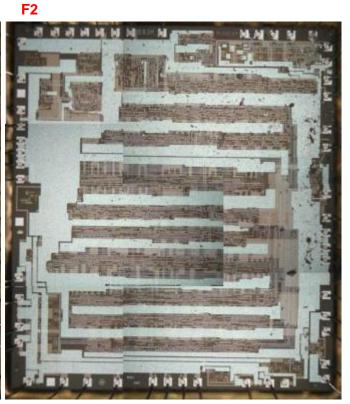
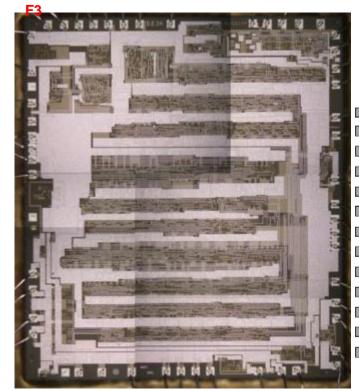


Figure 24 F3 => Typical I-V Curve of a leaking pin (Pin 44) to GND (Pin 48).

F1





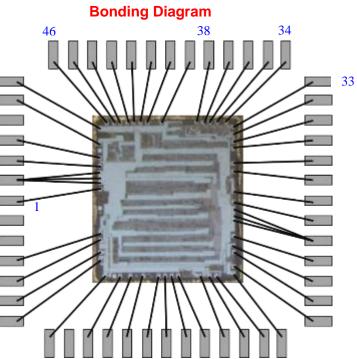


Figure 25 F1, F2 and F3 photographs of die surfaces and bonding diagram. No anomaly was observed.

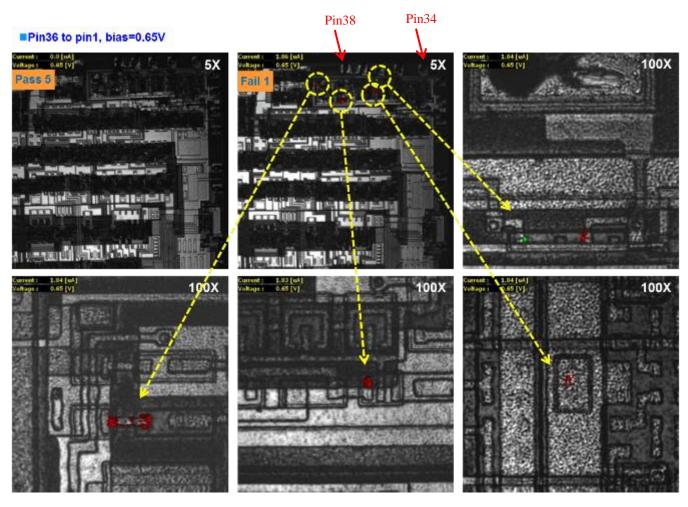


Figure 26 F1 => OBRICH analysis of failing sample 1. Hot spots are shown in Red and Green colors. Upper left photo represents a Ref sample. No emission site is observed on the Reference sample.

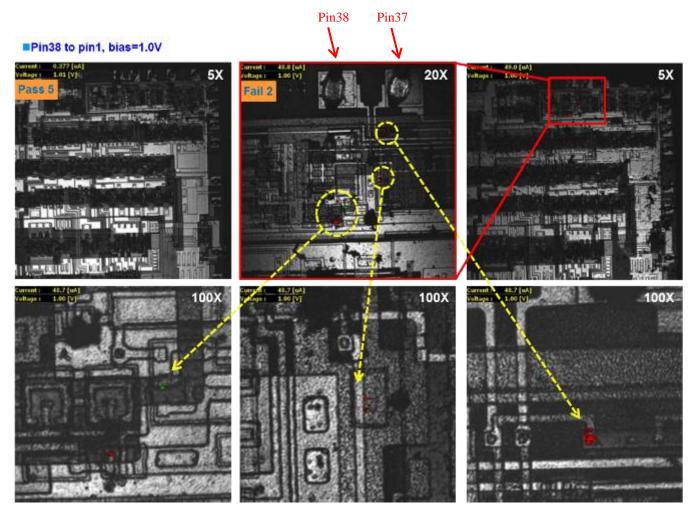


Figure 27 F2 => OBRICH analysis of failing sample 2. Hot spots are shown in Red and Green colors. Upper left photo represents a Ref sample. No emission site is observed on the Reference sample.

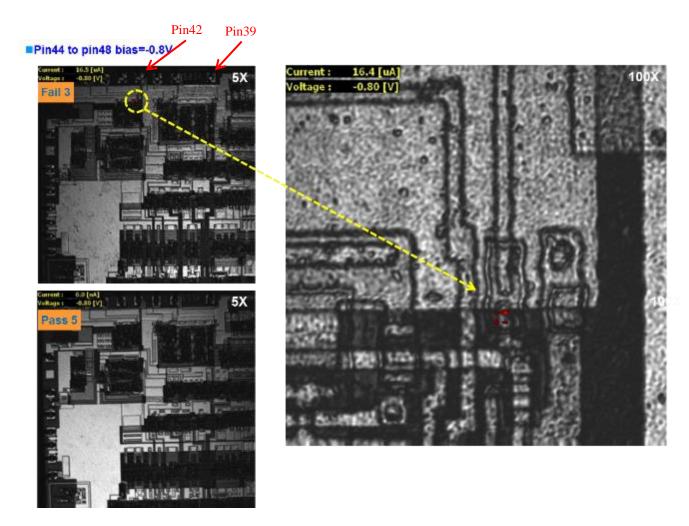


Figure 28 **F3** => OBRICH analysis of failing sample 3. Hot spots are shown in Red color. Lower left photo represents a Ref sample. No emission site is observed on the Reference sample.

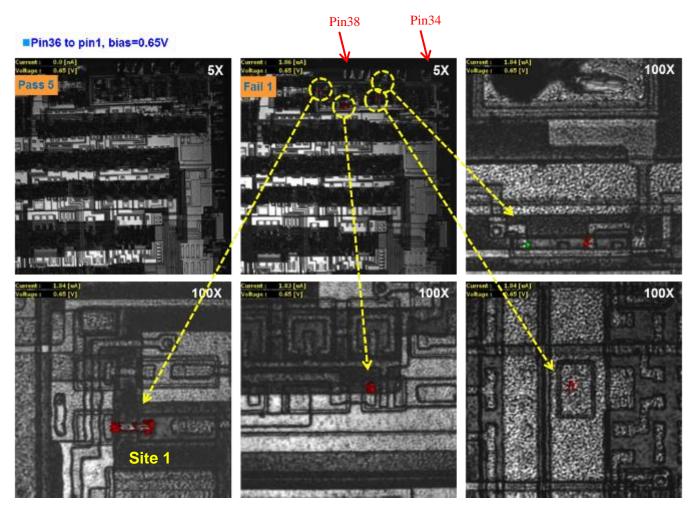


Figure 29 F1 => OBRICH analysis of failing sample 1. Hot spots are shown in Red and Green colors. Upper left photo represents a Ref sample. No emission site is observed on the Reference sample.

Site 1 was selected for mechanical delayering

Delayer and OM Inspection of F1 Sample (M2 Layer)

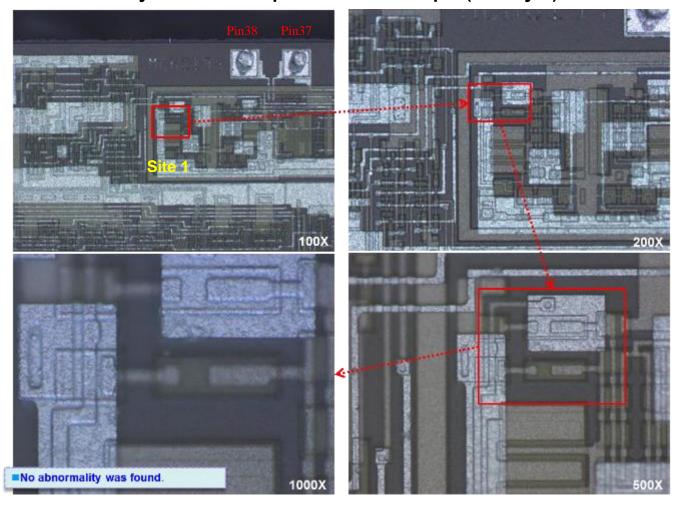


Figure 30 F1 => Close up photos of Site 1 on M2 layer. No anomaly was observed.

Delayer and OM Inspection of F1 Sample (M1 Layer)

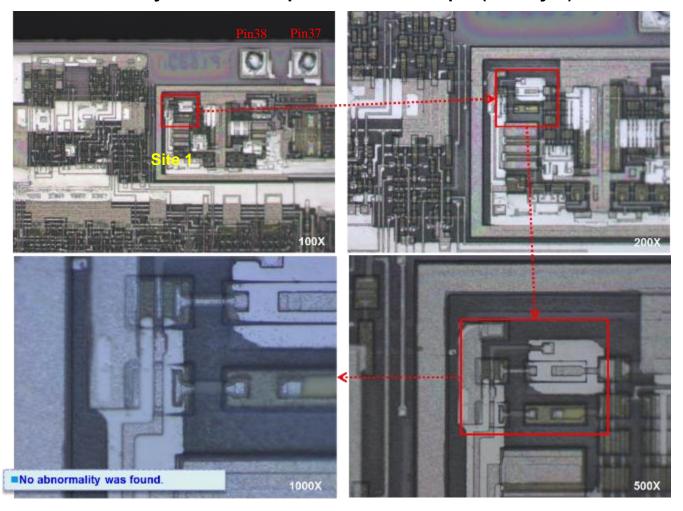


Figure 31 F1 => Close up photos of Site 1 on M1 layer. No anomaly was observed.

Delayer and OM Inspection of F1 Sample (Contact Layer)

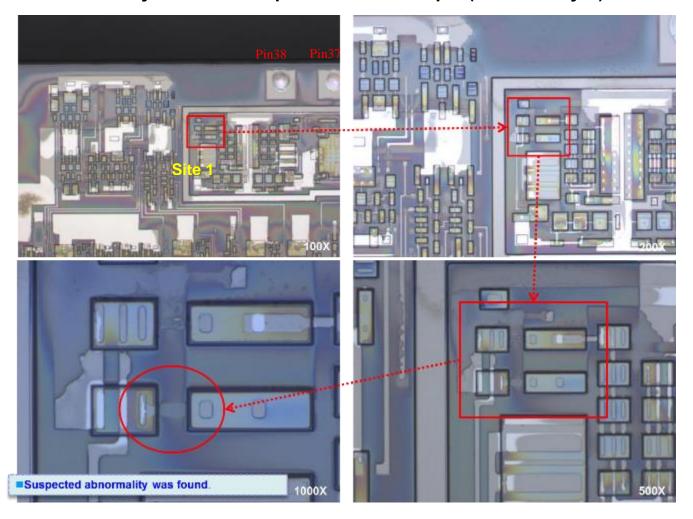


Figure 32 F1 => Close up photos of Site 1 on Contact layer. An anomaly was observed. Anomaly area is shown in red circle. Most likely cause of anomaly is ESD.

Delayer and SEM Inspection of F1 Sample (Poly Layer)

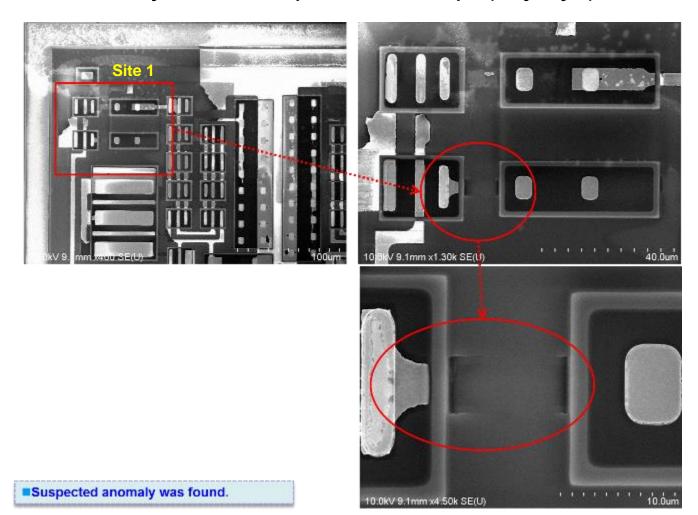


Figure 33 F1 => Close up SEM photos of Site 1 on Poly layer. An anomaly was observed. Anomaly area is shown in red circle. Most likely cause of anomaly is ESD.

■Pin38 to pin1, bias=1.0V

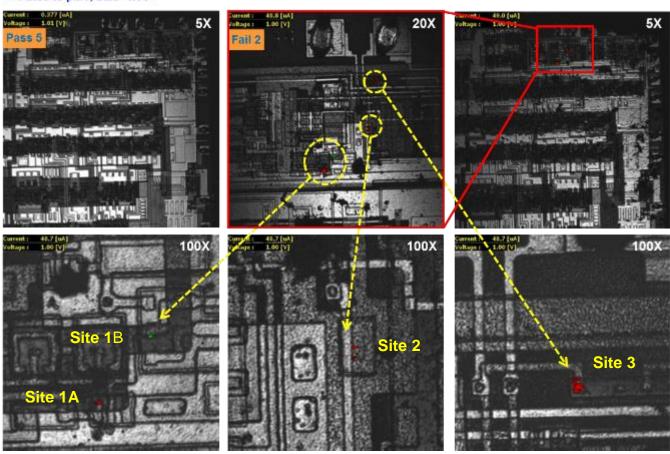


Figure 34 F2 => OBRICH analysis of failing sample 2. Hot spots are shown in Red and Green colors. Upper left photo represents a Ref sample. No emission site is observed on the Reference sample.

Site 3 was selected for mechanical delayering

Delayer and OM Inspection of F2 Sample (M2 Layer)

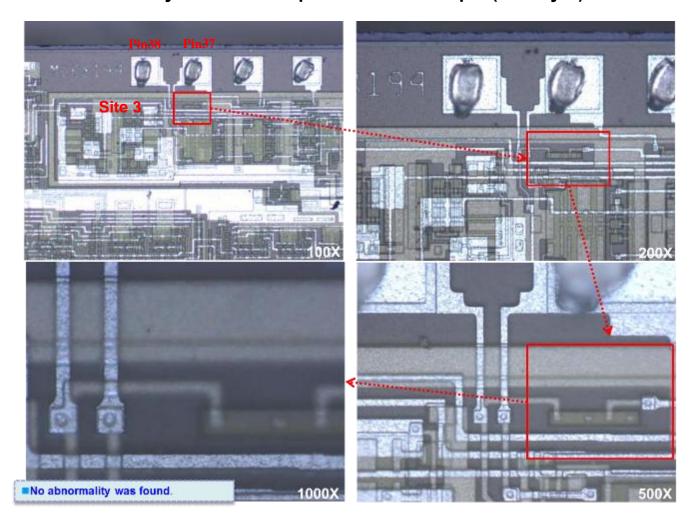


Figure 35 F2 => Close up photos of Site 3 on M2 layer. No anomaly was observed.

Delayer and OM Inspection of F2 Sample (M1 Layer)

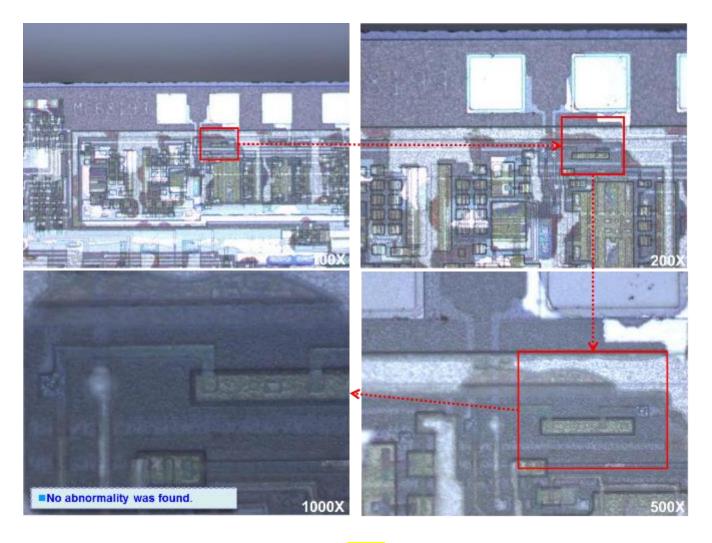


Figure 36 F2 => Close up photos of Site 3 on M1 layer. No anomaly was observed.

Delayer and OM Inspection of F2 Sample (Contact Layer)

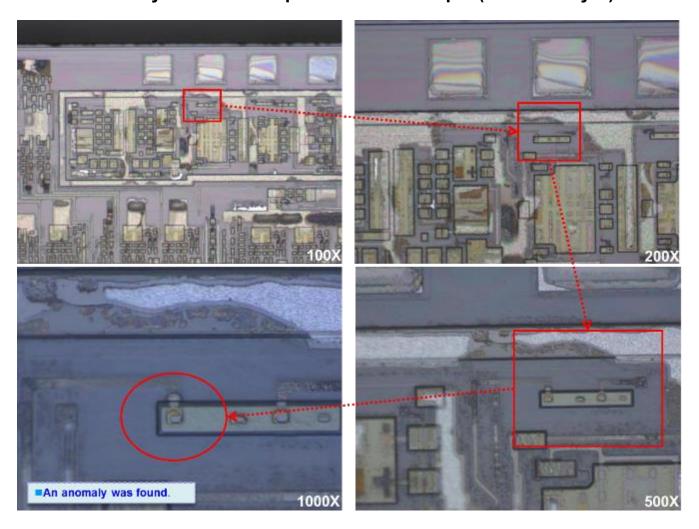


Figure 37 F2 => Close up photos of Site 3 on Contact layer. An anomaly was observed. Anomaly area is shown in red circle. Most likely cause of anomaly is ESD.

Delayer and SEM Inspection of F2 Sample (Poly Layer)

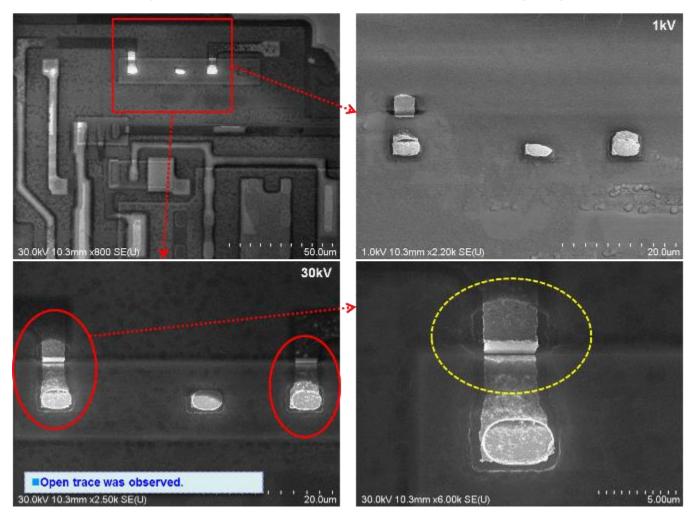


Figure 38 F2 => Close up SEM photos of Site 3 on Poly layer. Open traces were observed. Open traces are shown in circles. Most likely cause of the open is ESD.

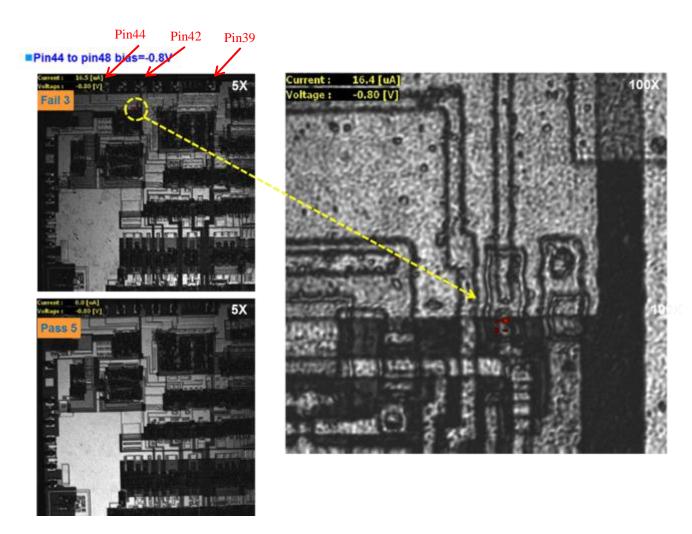


Figure 39 **F3** => OBRICH analysis of failing sample 3. Hot spots are shown in Red color. Lower left photo represents a Ref sample. No emission site is observed on the Reference sample.

Delayer and OM Inspection of F3 Sample (M2 Layer)

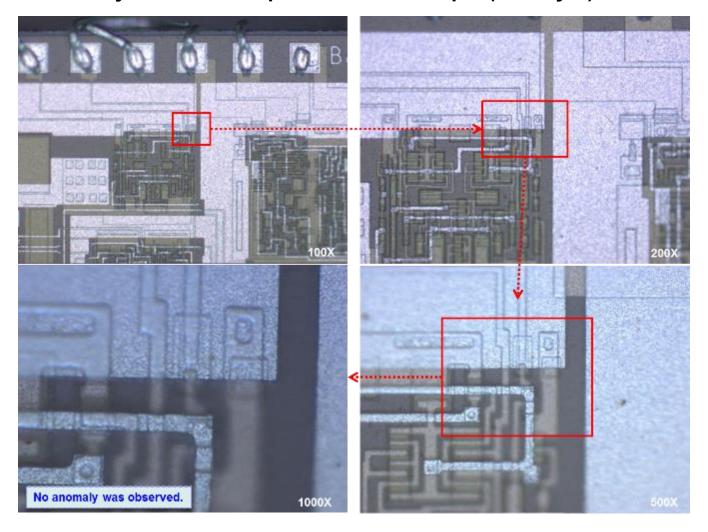


Figure 40 F3 => Close up photos of M2 layer. No anomaly was observed.

Delayer and OM Inspection of F3 Sample (M1 Layer)

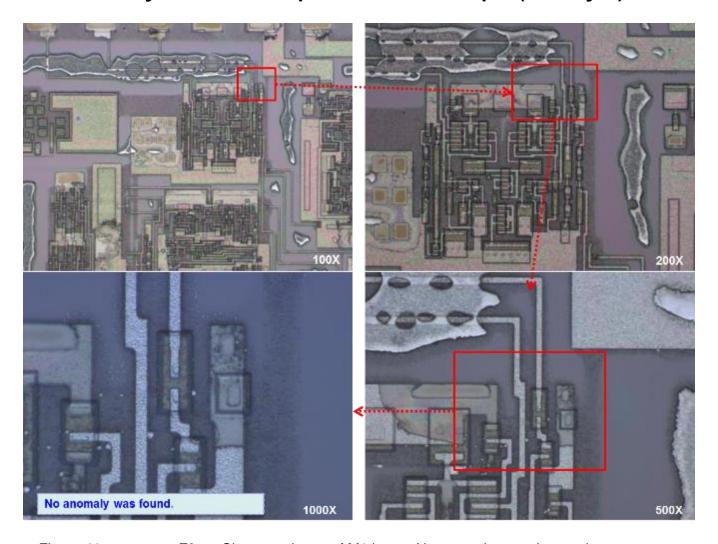


Figure 41 F3 => Close up photos of M1 layer. No anomaly was observed.

Delayer and OM Inspection of F3 Sample (Contact Layer)

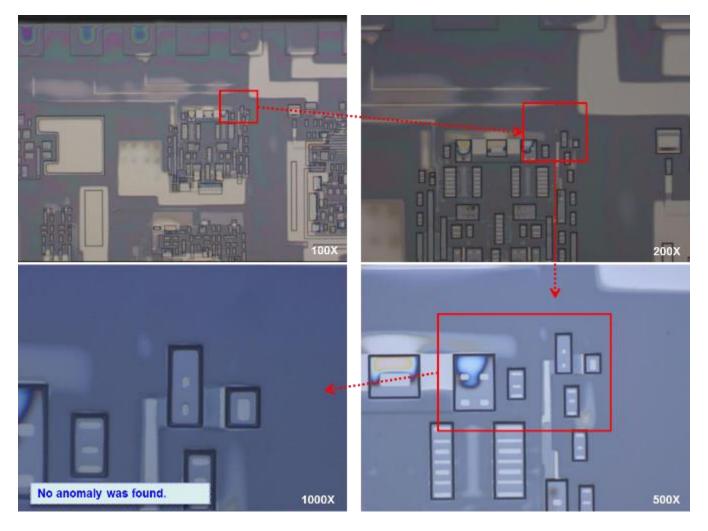


Figure 42 F3 => Close up photos of Contact layer. No anomaly was found.

Delayer and SEM Inspection of F3 Sample (Poly Layer)

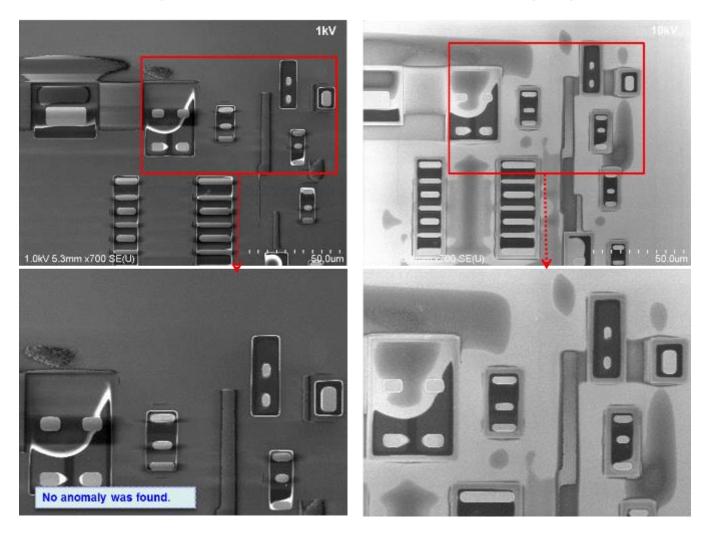


Figure 43 F3 => Close up SEM photos of Poly layer. No anomaly was observed

Delayer and SEM Inspection of F3 Sample (Substrate Layer)

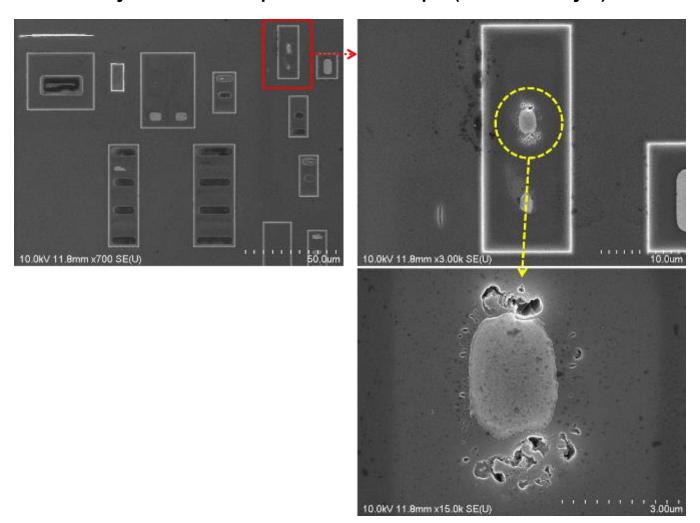


Figure 44 F3 => Close up SEM photos of Substrate layer. A damage site was observed. The damage site is shown inside the yellow circle. Most likely cause of damage is ESD.